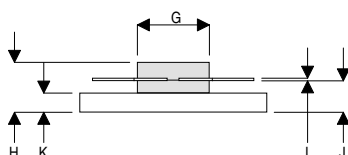
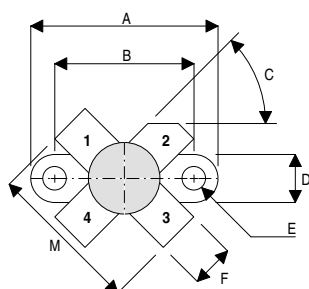


## MECHANICAL DATA



DA

PIN 1 SOURCE PIN 2 DRAIN  
PIN 3 SOURCE PIN 4 GATE

DIM	mm	Tol.	Inches	Tol.
A	24.76	0.13	0.975	0.005
B	18.42	0.13	0.725	0.005
C	45°	5°	45°	5°
D	6.35	0.13	0.25	0.005
E	3.17	0.13	0.125 DIA	0.005
F	5.71	0.13	0.225	0.005
G	9.52	0.13	0.375	0.005
H	6.60	REF	0.260	REF
I	0.13	0.02	0.005	0.001
J	4.32	0.13	0.170	0.005
K	2.54	0.13	0.100	0.005
M	20.32	0.25	0.800	0.010

# GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 20W – 50V – 175MHz SINGLE ENDED

## FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW  $C_{rss}$
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 16 dB MINIMUM

## APPLICATIONS

- HF/VHF COMMUNICATIONS  
from 1 MHz to 175 MHz

ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$P_D$	Power Dissipation	50W
$BV_{DSS}$	Drain – Source Breakdown Voltage	125V
$BV_{GSS}$	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	3A
$T_{stg}$	Storage Temperature	$-65$ to $150^{\circ}C$
$T_j$	Maximum Operating Junction Temperature	$200^{\circ}C$

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

## ELECTRICAL CHARACTERISTICS ( $T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$BV_{\text{DSS}}$ Drain–Source Breakdown Voltage	$V_{\text{GS}} = 0$ $I_{\text{D}} = 100\text{mA}$	125			V
$I_{\text{DSS}}$ Zero Gate Voltage Drain Current	$V_{\text{DS}} = 50\text{V}$ $V_{\text{GS}} = 0$			1	mA
$I_{\text{GSS}}$ Gate Leakage Current	$V_{\text{GS}} = 20\text{V}$ $V_{\text{DS}} = 0$			1	$\mu\text{A}$
$V_{\text{GS(th)}}$ Gate Threshold Voltage*	$I_{\text{D}} = 10\text{mA}$ $V_{\text{DS}} = V_{\text{GS}}$	1		7	V
$g_{\text{fs}}$ Forward Transconductance*	$V_{\text{DS}} = 10\text{V}$ $I_{\text{D}} = 0.5\text{A}$	0.8			S
$G_{\text{PS}}$ Common Source Power Gain	$P_{\text{O}} = 20\text{W}$	16			dB
$\eta$ Drain Efficiency	$V_{\text{DS}} = 50\text{V}$ $I_{\text{DQ}} = 0.1\text{A}$	50			%
VSWR Load Mismatch Tolerance	$f = 175\text{MHz}$	20:1			—
$C_{\text{iss}}$ Input Capacitance	$V_{\text{DS}} = 50\text{V}$ $V_{\text{GS}} = -5\text{V}$ $f = 1\text{MHz}$			60	pF
$C_{\text{oss}}$ Output Capacitance	$V_{\text{DS}} = 50\text{V}$ $V_{\text{GS}} = 0$ $f = 1\text{MHz}$			25	pF
$C_{\text{rss}}$ Reverse Transfer Capacitance	$V_{\text{DS}} = 50\text{V}$ $V_{\text{GS}} = 0$ $f = 1\text{MHz}$			1.5	pF

\* Pulse Test: Pulse Duration = 300  $\mu\text{s}$  , Duty Cycle  $\leq 2\%$

## HAZARDOUS MATERIAL WARNING

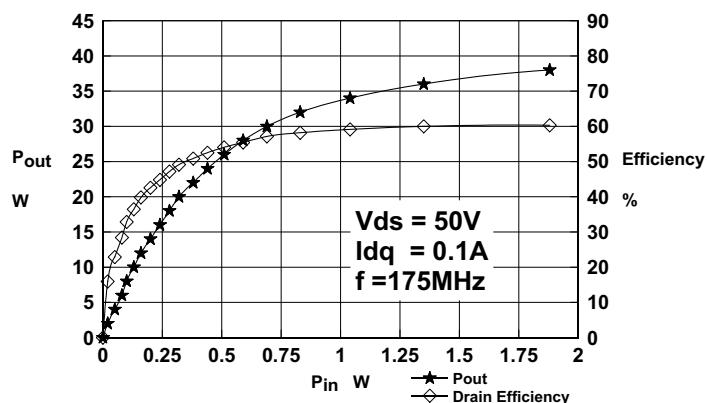
The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

## THERMAL DATA

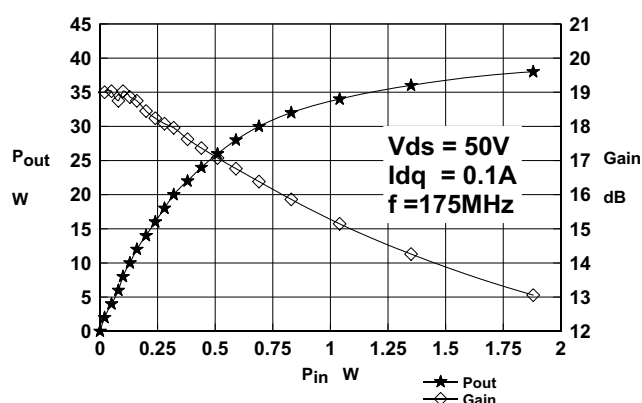
$R_{\text{THj-case}}$	Thermal Resistance Junction – Case	Max. 3.5°C / W
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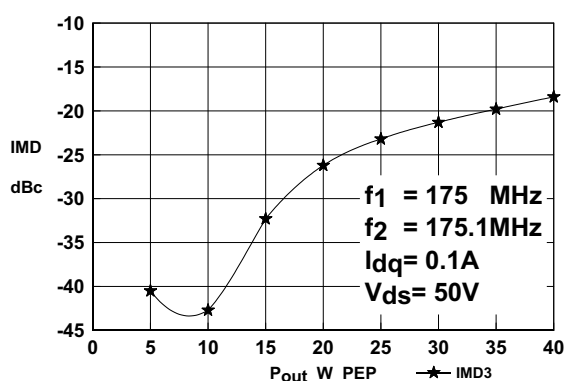
**Figure 1**

Power Output and Efficiency vs. Power input



**Figure 2**

Power Output and Gain vs Power Input



**Figure 3**

IMD3 vs Power Output

## OPTIMUM SOURCE AND LOAD IMPEDANCE

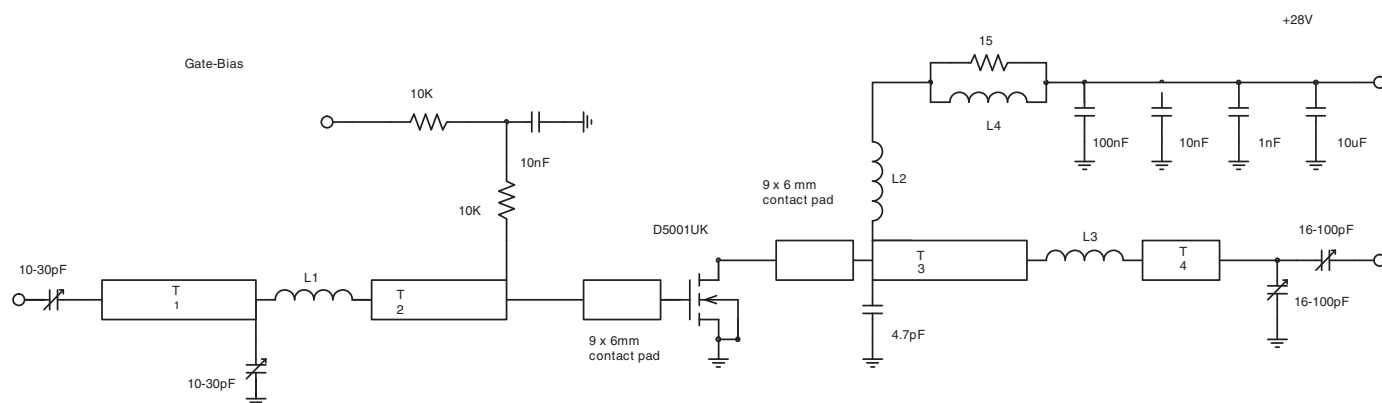
Frequency MHz	Z <sub>S</sub> Ω	Z <sub>L</sub> Ω
175	9.5 + j14.1	12.3 + j10.2

## Typical S Parameters

! Vds=50V Idq=0.6A  
# MHZ S MA R 50

!Freq !Mhz	S11 mag ang	S21 mag ang	S12 mag ang	S22 mag ang
60	0.837 -113.1	10.72 137.1	0.02 55.2	0.699 -72.6
70	0.835 -116	9.915 130	0.021 50.7	0.689 -74.4
80	0.833 -118	9.28 125.4	0.022 47.6	0.678 -78.1
90	0.831 -120	8.645 119.1	0.023 44.6	0.673 -80.6
100	0.829 -123.3	8.177 115.4	0.023 42.7	0.671 -83.6
110	0.828 -125.2	7.747 110.3	0.023 40.5	0.671 -85.3
120	0.825 -127.4	7.361 105.2	0.023 40.2	0.669 -87.9
130	0.823 -130	6.915 100.7	0.023 39.8	0.665 -88.6
140	0.82 -131.9	6.564 96.3	0.022 39.9	0.664 -89.6
150	0.816 -135	6.126 91.8	0.021 40.6	0.663 -91.4
160	0.81 -137.6	5.839 88.4	0.021 41.9	0.664 -92.6
170	0.807 -139.8	5.396 84.8	0.02 44.2	0.665 -94.2
180	0.803 -142.8	5.034 80.6	0.019 48	0.665 -96.8
190	0.804 -144.7	4.753 78.4	0.019 52	0.667 -98.6
200	0.806 -147.3	4.479 75.2	0.019 57.2	0.671 -101.2
210	0.803 -149.2	4.273 73.7	0.019 62.2	0.672 -103
220	0.808 -151.5	4.173 71.9	0.02 68.2	0.671 -103.5
230	0.802 -153.1	4.04 69.8	0.02 71.6	0.677 -105.6
240	0.807 -155.2	3.823 66.8	0.021 76.1	0.685 -107.9
250	0.811 -156.7	3.647 64.4	0.022 79.4	0.687 -109.9
260	0.812 -158.9	3.446 61.4	0.023 84.1	0.698 -111.9
270	0.814 -160.4	3.301 59.2	0.025 87.4	0.706 -113.7
280	0.818 -161.7	3.129 56.9	0.027 91.3	0.716 -116.2
290	0.823 -164	2.972 55.4	0.029 95.1	0.722 -119.2
300	0.828 -165.4	2.876 54.7	0.032 97	0.724 -120
310	0.828 -166.3	2.809 53.3	0.035 98.2	0.726 -122.1
320	0.829 -168.2	2.764 50.9	0.038 97.5	0.735 -123.7
330	0.832 -169.5	2.661 47.5	0.04 96.9	0.743 -125.4
340	0.835 -170.9	2.547 45.7	0.042 97.3	0.747 -127.4
350	0.838 -171.9	2.392 42.6	0.044 97.7	0.756 -130
360	0.843 -173.6	2.271 40.2	0.045 98.3	0.761 -130.8
370	0.843 -174.9	2.134 39.2	0.048 100.3	0.767 -133.3
380	0.845 -175.5	2.04 38.4	0.051 100.7	0.772 -134.4
390	0.852 -176.8	1.919 38.2	0.055 101.6	0.779 -137
400	0.857 -178.2	1.877 39.6	0.059 102.6	0.788 -138.4
410	0.862 -178.9	1.858 38.6	0.062 101.6	0.793 -139.8
420	0.862 179.2	1.817 36.5	0.066 99.6	0.797 -141.6
430	0.861 178.7	1.768 34.4	0.068 98.7	0.801 -143.8
440	0.873 177.3	1.697 32.6	0.07 97.2	0.809 -145.3
450	0.868 176.3	1.639 31.4	0.072 96.9	0.814 -147
460	0.871 174.9	1.566 29.4	0.074 96.8	0.822 -148
470	0.875 175.2	1.519 28.6	0.077 97.3	0.821 -149.6
480	0.875 174.4	1.456 28.1	0.08 96.9	0.83 -150.6
490	0.878 172.8	1.417 27.7	0.083 97.1	0.829 -152.2
500	0.882 171.6	1.367 27.2	0.086 96.5	0.841 -153.6

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## D5001UK 175MHz TEST FIXTURE

**Substrate 1.6mm PTFE/glass, Er = 2.5**

**All microstrip lines W= 4.4mm**

**T1 10mm**

**T2 13mm**

**T3 12mm**

**T4 4mm**

**L1 1.5 turns 22swg enamelled copper wire, 6mm id.**

**L2 10 turns 19swg enamelled copper wire , 6mm id.**

**L3 1.5 turns 22swg enamelled copper wire, 6mm id.**

**L4 13.5 turns 19swg enamelled copper wire on Siemens B64920A618x830 ferrite core**